

*Crystal Growth  
from  
High-Temperature  
Solutions*

D. Elwell and H. J. Scheel

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## Index

### A

- absorption, infrared 501  
accelerated crucible rotation technique (ACRT) 13, 228, 256, 270, 273, 290, 291, 295, 296, 299, 300, 302, 305, 326, 327, 386–395, 401–403, 418, 420, 448.  
acid-base concept 79, 84, 106  
activity 62  
adsorption layer (see also surface adsorption) 170, 171, 174, 323  
aluminium oxide 9, 10, 28, 33, 34, 68, 70, 75, 78, 79, 88, 90, 93, 95–97, 100, 107, 123, 215–220, 296, 297, 337, 349, 360–365, 418, 420, 504, 523, 537, 560, 561  
amalgam method 419  
anisotropy  
    facet-related 229  
    growth-induced 441  
atmosphere control 330, 331, 379–381  
atomic absorption spectroscopy 475, 478, 479, 494

### B

- back-stress effect 165, 176  
barium titanate 3, 9, 17, 31, 88, 93, 96, 97, 106, 107, 119, 123, 220, 283, 287, 296, 297, 299, 308, 370, 374, 401, 417, 476, 526, 537, 562–564  
BCF (Burton-Cabrera-Frank) theory 160–166, 170, 171, 173, 174, 176, 189, 212, 249, 252  
Berg-Barrett technique 520–524  
beryllium oxide 223, 296, 337, 501, 505, 523, 526, 564, 565

Bormann technique 521–523, 525

- boundary layer  
    diffusion 149, 151–156, 165, 166, 173, 174, 243, 253, 268, 301, 304, 328, 382, 459  
    hydrodynamic 151  
    thermal 253, 261  
thickness 152–156, 174, 252, 253, 328, 386, 395, 460, 461, 489, 490  
bubble-domain devices (see magnetic bubble-domain devices)  
bunching of steps 183, 188, 189  
Burton-Prim-Slichter equation 268, 323, 324, 489, 490  
butterfly twin 220, 296, 401, 417, 476, 526

### C

- characterization 2, 32, 73  
chemical 89–92, 472–499  
general 9, 10, 470–557  
standard 544, 545  
structural 499–512  
chemical transport reactions 7, 10, 316  
chemical vapour deposition (CVD) 7, 14, 316  
chemicals 375–379  
choice of solvent 86–95  
chromatography 489  
cluster 16, 140, 144, 148, 149  
colorimetry 475, 477, 484  
colour centres 514, 531  
complex formation 16, 70, 72, 81–84, 101–106, 113, 170, 211, 215, 228, 229, 281, 282, 291, 292, 416  
complexes 82, 211

- complexity of compounds 280–282, 291  
 computer in laboratory automation 350, 355, 433, 471, 487, 509, 510  
 computer simulation 146, 160, 170  
 constitutional supercooling (see also growth rate, maximum stable; morphological stability) 237, 239–241, 255, 262, 307, 456  
 convection  
   forced (see also ACRT; solution flow rate; stirring; TSSG) 269–274, 280–284, 293, 301, 369, 370, 381–396  
   natural (thermal) 267, 269–272, 290, 293, 299, 301, 321, 323, 370, 381, 383, 386, 447  
   solutal 269, 299, 381, 383, 447, 460  
 convection-free cell 270, 272, 317, 383  
 coulomb interactions (see also ionic interactions) 60, 66, 70  
 coulometry 475  
 critical nucleus 141, 238  
 crucible materials 292, 311, 313, 356–372, 404, 463  
 crucible size 30, 31, 266, 368–370  
 crystals, applications (see also ferroelectric crystals, laser, etc.) 11–15, 203  
 crystal growth  
   from aqueous solutions 7, 278, 280, 281, 284, 383  
   from gels 7, 8  
   from high-pressure solutions 6, 8, 10, 14, 25, 112, 113, 122, 209, 329, 331, 396–399, 404–413, 416  
   from high-temperature solutions, definition 3–6  
   from melt 6, 10, 110  
   from solid state 6  
   from vapour 7, 10, 14, 110  
   history 3, 4, 20–49  
   large-scale 12–17, 419  
   rate (see growth rate)  
   theory 16, 138–198  
 crystal habit 24, 202–232  
 crystal handling 501  
 crystal morphology 147, 202–236  
 crystal orientation 510  
 crystal size, maximum 250, 251, 254  
 crystal-solution interface 139, 143, 149  
 Czochralski method 10, 349, 350, 364, 377, 384–386, 492, 506, 507

**D**

- defects in crystals (see also Frenkel, Schottky defects, etc.) 483, 505, 512–535  
 dendritic growth 22, 183–185, 198, 226, 229, 231, 263, 266, 402, 518  
 desolvation 149, 150, 169–172, 198, 255  
 diamond 15, 24, 35, 112, 127, 259, 317, 397–399, 404–411, 419, 565  
 differential thermal analysis (DTA) 116  
 diffusion boundary layer (see boundary layer, diffusion)  
 diffusion coefficient 461, 462, 536, 537  
 diffusional undercooling 240  
 dislocations 505, 512–517, 520, 522–525, 527, 535, 538–544  
 decorated 516  
 effect on growth (see screw dislocations)  
 effect on stability 250, 259  
 dislocation density 9, 10, 14, 257, 273, 284, 460, 462, 464, 504, 515, 524, 526, 538, 540  
 distribution coefficient 322–328, 446, 449, 486, 489, 493, 514, 533  
 double-crystal X-ray topography 521, 522, 524

**E**

- edge nucleation 185–189, 197, 263, 264, 408, 495  
 Ekman—layer flow 386, 388, 390, 391  
 electrocrystallization 15, 106, 112, 174, 213, 293, 301, 318–321, 330, 420  
 electrolysis 15, 16, 106, 108, 213, 330, 376, 416

- electron diffraction 510, 511  
 electron microscopy 180, 525–530, 535  
 electron paramagnetic resonance (EPR)  
   82, 484, 486, 531, 532  
 electron probe microanalysis 321, 322,  
   327, 475, 479–481, 493, 499, 528, 536  
 electron spectroscopy 481, 482, 484,  
   494  
 electro-optic crystals 14  
 embryos 140  
 emerald 25, 31, 34, 103, 105, 311, 312,  
   384, 418, 564  
 emissivity 348–350  
 enthalpy of fusion 62, 67  
 enthalpy of mixing 63  
 entropy of fusion 62, 67, 323  
 entropy of mixing 63  
 equilibrium form (-habit, -shape)  
   203–207, 211  
 etch figures, etch pits 189, 449, 525,  
   526  
 etching 503  
 evaporation method 24, 28, 78, 268,  
   279, 286, 293, 295, 297–300, 401
- F**
- faces  
   non-singular 207  
   singular 204, 207  
   vicinal 207, 248, 249, 274  
 facet formation 203  
 facet-related site selectivity 229  
 ferrimagnetic crystals (see rare-earth  
   garnets; yttrium iron garnet)  
 ferroelectric crystals 3, 7, 31, 220  
 F (flat) faces 205–207, 215  
 field-strength concept 65, 71, 72  
 flame-fusion method 10, 31, 110, 506,  
   507  
 flux growth, definition 4  
 flux-reaction technique 28, 29, 311,  
   312  
 free energy of  
   formation 75, 76  
   mixing 61, 63, 64, 67  
 Frenkel defect 513  
 fugacity 62  
 furnace design 332–340  
 fused salts 59
- G**
- gadolinium gallium garnet (GGG)  
   444, 574  
 gallium arsenide 3, 14, 109, 126, 256,  
   302, 303, 308, 316, 317, 328, 435–440,  
   442, 443, 447, 455–460, 485, 510,  
   537, 538, 572  
 gallium phosphide 3, 80, 109, 126,  
   308, 309, 312, 313, 315, 317, 320,  
   327, 328, 419, 435–440, 444, 460,  
   464, 573  
 garnets, magnetic (see also rare-earth  
   garnets; yttrium iron garnet) 3  
 gemstone(s) 3, 15, 20, 23–25, 31, 408,  
   410, 535  
 Gibbs-Thomson equation 245  
 Gilmer-Ghez-Cabrera theory 168–170,  
   174  
 gradient-transport technique (see tem-  
   perature gradient transport)  
 gravimetry 475  
 growth hillocks (see also surface  
   morphology) 183, 184, 187–190,  
   193, 194, 220, 225, 227, 255, 257,  
   274, 495, 530  
 growth history 538–544  
 growth rate  
   effective 294, 297, 301, 315, 459,  
   461  
   linear 142, 152, 155–157, 160,  
   164–178, 238, 245, 247, 265, 266,  
   268, 309, 442, 444  
   maximum stable (see also mor-  
    phological stability) 10, 156, 176,  
    189, 237, 238, 241, 242, 251–261,  
    264–268, 274, 284, 286, 293, 307,  
    310, 382, 399, 408, 447, 492, 496  
   stable 87, 156, 176, 237, 264, 286,  
    290, 299, 304, 307, 369  
   ultimate stable 255–257, 274, 293  
   unstable 183–185, 261–264, 518,  
    519, 535

growth spirals 158–166, 171, 176–183, 189, 198, 220, 248, 408, 409, 501  
 polygonized 180  
 Guinier-Tennevin technique 520, 521, 524

**H**

habit faces 147  
 habit modification 109, 147, 148, 202–236, 417, 418  
 Hartman and Perdok (PBC) concept 146, 147, 181, 205  
 heat of crystallization 150  
 heat of fusion 62, 64  
 heat of solution 69  
 heat pipes 339, 340  
 heating elements 332–339  
 Henry's law 62  
 high temperature solutions  
   ionic interactions (see ionic interactions)  
   structure of 59–95, 110

hillocks (see growth hillocks)  
 hollow crystals 185, 224, 229, 231  
 hopper growth 185, 263  
 hot-stage microscopy 115  
 hydration energy 69, 70  
 hydrodynamic boundary layer (see boundary layer, hydrodynamic)  
 "hydroflux" method 416  
 hydrothermal growth (see crystal growth from high-pressure solutions)

**I**

ideal solvent 87  
 identification 507, 508, 527  
 immiscibility 65, 71, 102, 104, 108  
 impurities, effect on habit 208, 210–215, 217–220, 224, 228, 230, 231  
 impurities, incorporated 89–91, 94, 203, 211, 217, 218, 220, 222, 228, 231, 262, 286, 295, 298, 321–329, 370, 372, 383, 408, 463, 476, 479, 486–499, 509, 532  
 impurity incorporation, facet-related

(see also site selectivity, facet-related) 257, 490  
 inclusions 29, 61, 89, 90, 183–185, 210, 225–228, 231, 237, 244, 247, 258–263, 267, 284, 285, 307, 310, 324, 331, 505, 513, 515, 518–520, 525, 526, 534–540, 544  
 inclusions, removal 536–538  
 incongruent melting 4  
 induction heating 332, 338, 339, 348  
 interface kinetics (see also surface kinetics) 148–152, 156–183, 238, 239, 247, 248, 252, 253, 258, 273, 310, 460  
 ion microprobe 483, 494  
 ionic interactions (see also coulomb interactions) 60, 66, 70  
 Ising model 145  
 isothermal-solution-mixing (ISM) technique 314, 457, 458

**J**

Jackson( $\alpha$ ) factor 145, 146

**K**

K (kinked) faces 205–207, 215  
 kink, definition 148, 149  
 kink poisoning 212, 213  
 Kossel-Stranski model 205, 206, 211

**L**

Lang technique 521–525, 544  
 laser crystals (see also ruby, semiconductor laser) 9, 14, 31, 107, 324, 466  
 lattice-constant determination 484, 485, 508–510, 522  
 lattice energy 7, 69, 70  
 Laue photograph 519, 520  
 Lewis acid-base concept 70, 320  
 light-emitting diode (LED) 3, 14, 309, 433–438, 444, 455, 466  
 light scattering 535  
 liquid phase epitaxy (LPE) 5, 12–14, 17, 109, 203, 229, 256, 268, 284, 313, 326, 356, 383, 412, 418, 420, 433–466, 493, 534

- localized cooling 289–291, 295, 313, 339, 388, 392, 402, 420  
 low-angle grain boundaries 194, 216, 513, 516, 517, 519  
 low energy electron diffraction (LEED) 511, 529  
 luminescence analysis (see also optical fluorescence analysis) 494, 519
- M**
- macrospirals 180–182, 189  
 macrosteps 183  
 magnetic bubble-domain devices 13, 14, 121, 229, 286, 324–326, 433, 440–442, 444, 501, 510  
 magneto-optic crystals 12  
 mass spectrometry 475, 482, 483, 488, 494  
 materials information centres 11  
 metastable phases, growth of 112, 121, 122, 320, 329, 330, 405, 413  
 metastable region (see also Ostwald-Miers region; undercooling, metastable) 61, 84, 85, 94, 102, 121, 139, 279–293, 381, 382, 416, 449, 450  
 microscopy  
   infrared 501, 535  
   optical 499–506, 519, 535  
     interference 501  
     phase contrast 501  
 mineralizer 29, 95, 411, 419  
 molybdenum disilicide 332–336  
 morphological stability (see also growth rate, maximum stable; constitutional supercooling) 24, 85, 237, 249  
 mosaic structure 516, 517, 519, 522–524  
 Mössbauer effect 82, 484, 486, 511, 532
- N**
- neutron activation analysis 475, 487  
 neutron diffraction 72, 510  
 nonstoichiometry 73–77, 472, 483–486, 510, 512, 513
- nuclear magnetic resonance (NMR) 72, 511  
 nucleation 9, 112, 139  
   edge 185–189  
   effect of solution flow 280–282, 290  
   heterogeneous 140, 143, 280, 292  
   homogeneous 140, 143, 280  
   spontaneous 105, 121, 183, 198, 226, 255, 266, 273, 280, 281, 284, 287, 290, 291, 293, 295, 296, 381, 382, 384, 450  
 surface 148, 156–160, 189, 212–214, 216  
 two-dimensional 148, 156–160, 187, 212–214, 216, 451  
 nucleation control 85, 279–293, 295, 296, 302, 303, 392–395, 402, 403  
 nucleation rate 141–143, 157, 197  
 nucleus, critical radius 140, 141, 157, 158, 238, 239, 273, 280
- O**
- optical absorption spectroscopy 511, 519  
 optical crystals 3  
 optical emission spectroscopy 475, 477, 478, 487, 494  
 optical fluorescence analysis (see also luminescence analysis) 488, 506  
 Ostwald's law of successive transformations 121, 329  
 Ostwald-Miers region (see also nucleation rate; metastable region) 279–292, 381
- P**
- partial molar quantities 61  
 periodic bond chain (PBC) concept 146–148, 181, 197, 205, 206, 214  
 perturbation theory 244–248  
 phase diagrams 71, 73, 80, 83, 84, 107, 113, 122–127  
   determination 79, 113–127  
 phase transitions 220, 512, 531, 532  
 philosopher's stone 26

photo-emission electron microscopy 528–530  
 PID control 350–355  
 piezoelectric crystals 7, 31  
 platinum handling 292, 333, 338, 341–347, 356–365, 367–372  
 polarizability 66, 70, 72, 84, 92, 101  
 polarography 475, 477  
 precipitates 518, 520, 526  
 proportional control 350–355  
 purification 311, 323, 375–380  
 pyrometry 340, 348–350

**R**

radiography 536  
 Raman spectroscopy 72, 81, 519  
 Raoult's law 63–66  
 rare-earth garnets 3, 9, 12, 31, 79, 93, 96, 97, 101, 102, 105, 187, 188, 226–229, 291, 292, 324–327, 330, 392, 413, 418, 440–442, 449, 451, 570, 574, 581, 584, 585, 588, 590, 594  
 rate-determining process 151, 164–176, 198, 459, 460  
 Rayleigh number 269, 270  
 reaction equilibria 79  
 reaction method 293, 301, 328  
 reciprocal salt systems 80, 92–94  
 redox equilibria 73, 74, 78, 79  
 repeatable step 205  
 resistance heating 332–338  
 resistance thermometry 340–343, 346  
 retrograde solubility 66  
 Richard's rule 67, 68  
 ruby 3, 9, 14, 15, 24, 25, 28, 30, 31, 33, 74, 107, 123, 215, 297, 321, 503, 505, 506, 560, 561

**S**

salting out effect 293, 314  
 sawing 501  
 scanning electron microscopy 480, 527, 528, 535  
 Schottky defects 513  
 Schulz technique 520, 521, 524

screw dislocation (see also spiral growth mechanism) 158–160, 165, 176–183, 189, 194, 198, 220, 225, 227, 286, 517, 523, 541  
 seed crystal 267, 282, 284, 286, 287, 291, 292, 301–305, 309, 313, 369, 383, 385, 392, 393, 396, 402, 403, 407, 418, 538–541  
 mounting 286–288  
 segregation 322, 323  
 semiconductor crystals (see also gallium arsenide and phosphide; silicon) 14, 16, 108–113, 126, 127, 317, 320, 356  
 semiconductor laser 14, 433, 437–440, 466  
 shifting-equilibrium technique 293, 314  
 silicon 3, 108, 127, 308, 317, 349, 364, 587  
 silicon carbide 110, 111, 308, 317, 330, 332–338, 366, 416, 418, 420, 436, 437, 537, 538, 587  
 site preference 229  
 site selectivity, facet-related 229, 286, 324, 408,  
 slow-cooling method 28, 264–268, 279, 283, 287, 293–296, 420, 533  
 solar cells 466  
 solid solubility 73, 74, 78, 87–92, 110, 113  
 solid solutions, preparation of 295, 302, 304–307, 320–328, 331, 415  
 solubility (see also phase diagrams) 62–64, 66, 70, 81, 84–88, 92, 94, 105, 106, 108, 109, 122, 284, 356, 404, 405, 416  
 determination of 113–127, 328  
 retrograde 66, 298  
 solubility parameter 65  
 solution flow  
     effect on habit 208–210, 227  
     effect on stability 251–268, 272–274  
 solution flow-rate (see also ACRT; convection; stirring; TSSG) 151, 154, 171–173, 183, 381–384

- solutions  
associated 63, 67  
ideal 140  
ionic interactions in 60, 66, 112  
metallic 64, 72, 108–113, 126, 127,  
270, 286, 328, 366, 405  
non-ideal 63–66  
regular 63, 64, 72, 460  
structure of 59–95, 110  
viscosity of 281, 282  
solvation 63, 64, 69, 70, 81, 149, 207,  
209  
solvation (hydration) energy 69  
solvent additives 94, 95, 109, 112,  
210–215, 217–220, 224, 226, 228,  
231, 280, 281, 291, 292  
solvent, choice of 86–113  
solvent creeping 87, 105  
solvent properties 86–87, 95–113  
solvent-solute interaction (see solvation)  
spiral growth mechanism (see also  
BCF theory; growth spirals) 158–  
166, 176–183, 213, 220, 225  
spiral shearing flow 388–390  
stable growth (see growth rate, stable)  
stacking faults 517, 524–527  
step, definition 148, 149  
step pinning 213  
velocity 161–163, 165, 171, 177–  
183, 213, 214, 217  
S- (stepped) faces 205–207, 215  
stirring (see also convection, forced)  
269, 381–396, 399, 418, 447, 448,  
450, 453, 466  
stoichiometry, determination of 73–  
77, 472, 483, 486  
striations 262, 321, 322, 381, 383,  
395, 490–492, 495, 496, 498, 503,  
513, 523, 526  
supersaturation  
critical (see also metastable region)  
121, 140, 141, 174  
relative 141, 264, 293  
supersaturation gradient 151–154, 162,  
239–263, 273, 274, 284, 304, 446, 466  
supersaturation inhomogeneity 249  
surface adsorption 149, 156, 165, 170,  
174, 211–215, 220, 249, 323, 324  
surface diffusion 149, 161–174, 181,  
182, 198, 228, 238, 239, 247, 248,  
273, 323  
surface (free) energy 203–205, 210–  
212, 214, 228, 287  
surface kinetics (see also interface  
kinetics) 148–152, 156–183  
surface morphology (see also growth  
hillocks, growth spirals) 158–160,  
183–197, 255, 257, 382, 408, 460,  
501, 505, 526, 527  
surface nucleation 148  
surface roughness 145, 146, 148, 217  
surface steps 156  
surface tension 453
- T**
- Temkin ( $\gamma$ -) parameter 146  
Temkin's (solution) model 67, 68  
temperature control 264–268, 272,  
273, 284, 294, 295, 350–355, 370,  
381, 495  
temperature cycling 287–289, 295, 420  
temperature gradient  
in the crystal 4, 239–244, 252–255,  
261, 273, 274, 284, 285, 304  
in the solution 270, 271, 273, 289,  
301–310, 446  
temperature gradient transport tech-  
nique 279, 280, 284, 293, 295,  
300–311, 326, 327, 339, 392, 393,  
403, 407, 459, 533  
temperature oscillations 267, 269, 272,  
294, 299, 321, 370, 386, 490–492,  
494–496  
temperature programming 264–268,  
286, 289, 294, 306, 355, 369, 370  
thermistors 342  
thermoelectric thermometry, thermo-  
couples 340–348, 351–354, 399  
thermogravimetry 119, 484, 485  
thermoluminescence 519  
thermopile 343–345

thin alloy zone crystallization 257, 304, 306, 317  
 time markers 462  
 titrimetry 475, 484  
 top-seeded solution growth (TSSG) 102, 103, 107, 110, 222, 255, 256, 259, 261, 270, 273, 283–287, 295, 302, 303, 350, 384–386, 392, 420, 491  
 tracer, radioactive, techniques 475, 488  
 transmission electron microscopy 525–527  
 transport techniques 295, 300–320  
 travelling heater method (THM) 304, 307–309  
 travelling solvent method (TSM) 304, 308, 538  
 travelling solvent zone method 203, 270, 284, 301, 306, 311, 327, 339, 420, 459  
 twins, twinning 192, 210, 216, 217, 221–225, 309, 500, 503, 505, 507, 513, 517, 519, 523  
 twin-plane re-entrant edge (TPRE) mechanism 190–195, 216–225, 417

**U**

ultramicroscopy 501, 505, 535

ultrasonic

attenuation 532

dispersion 532, 535

ultrasound, effect on growth 210

undercooling, metastable (see also metastable region; critical supersaturation; Ostwald-Miers region) 121, 449, 450

**V**

vapour-liquid-solid (VLS) mechanism 6, 80, 110, 293, 310, 315–318, 328, 418, 420, 459

vapour-liquid-reaction-solid (VLRS) mechanism 29, 301, 313, 314  
 vibrations, effect on growth 244, 273  
 vicinal face(s) 207, 248, 249, 274  
 viscosity 82, 85–87, 100–102, 105, 416  
 volume diffusion (see also boundary layer, diffusion) 151–156, 165–176, 459, 462

**W**

wetting 446, 459  
 whiskers 224, 231, 293, 315–318, 418, 420  
 Wulff plot 204  
 Wulff theorem 203, 204

**X**

X-ray diffraction 72, 202, 507–510, 517, 526, 527  
 X-ray fluorescence analysis 475, 479, 484, 494  
 X-ray topography 95, 216, 250, 251, 286, 382, 504, 519–525, 535, 538–544

**Y**

yttrium aluminium garnet (YAG) 90, 95, 102, 125, 226–229, 282, 296, 324, 325, 327, 466, 504, 591  
 yttrium iron garnet (YIG) 9, 12, 13, 88, 93, 95–97, 102, 121, 125, 187, 189, 226–229, 255–257, 282, 284, 291, 292, 295, 296, 299, 304, 308, 324–327, 331, 370, 402, 403, 441, 449, 498, 503, 507, 510, 525, 526, 532–534, 591–593

**Z**

zone melting, zone refining 376